

Thyristor \ Diode Module

$V_{RRM} = 2 \times 1600 \text{ V}$

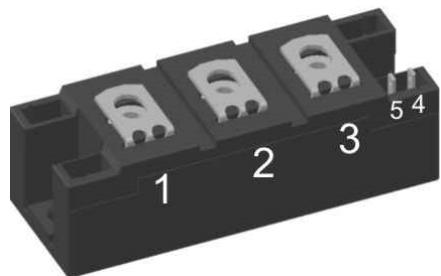
$I_{TAV} = 216 \text{ A}$

$V_T = 1.1 \text{ V}$

Phase leg

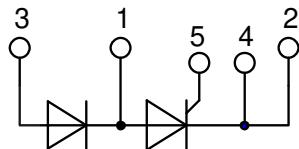
Part number

MCD200-16io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

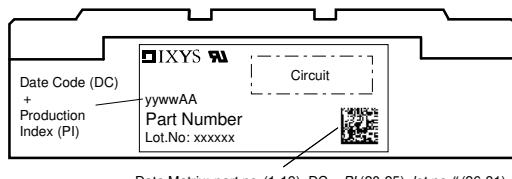
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Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1600 V$ $V_{R/D} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		400 15	μA mA
V_T	forward voltage drop	$I_T = 200 A$	$T_{VJ} = 25^\circ C$		1.20	V
		$I_T = 400 A$			1.52	V
		$I_T = 200 A$ $I_T = 400 A$	$T_{VJ} = 125^\circ C$		1.10 1.50	V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 125^\circ C$		216	A
$I_{T(RMS)}$	RMS forward current	180° sine			340	A
V_{T0}	threshold voltage	r_T slope resistance } for power loss calculation only	$T_{VJ} = 125^\circ C$		0.80	V
	slope resistance				1.4	$m\Omega$
R_{thJC}	thermal resistance junction to case				0.13	K/W
R_{thCH}	thermal resistance case to heatsink			0.05		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		770	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		8.00	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		8.64	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		6.80	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		7.35	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		320.0	kA^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		310.5	kA^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 125^\circ C$		231.2	kA^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		224.4	kA^2s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	366		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^\circ C$		120	W
		$t_p = 500 \mu s$			60	W
					20	W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 600 A$			100	$A/\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.5 A/\mu s;$				
		$I_G = 0.5 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 200 A$			500	$A/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		1000	$V/\mu s$
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		2	V
			$T_{VJ} = -40^\circ C$		3	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		150	mA
			$T_{VJ} = -40^\circ C$		220	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		0.25	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^\circ C$		200	mA
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ C$		2	μs
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 300 A; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 100^\circ C$		200		μs
		$di/dt = 10 A/\mu s$ $dv/dt = 50 V/\mu s$ $t_p = 200 \mu s$				

Package Y4

Conditions			min.	typ.	max.	Unit
I_{RMS}	<i>RMS current</i>	per terminal			300	A
T_{VJ}	<i>virtual junction temperature</i>		-40		125	°C
T_{op}	<i>operation temperature</i>		-40		100	°C
T_{stg}	<i>storage temperature</i>		-40		125	°C
Weight				150		g
M_D	<i>mounting torque</i>		2.25		2.75	Nm
M_T	<i>terminal torque</i>		4.5		5.5	Nm
$d_{Spp/App}$	<i>creepage distance on surface / striking distance through air</i>		<i>terminal to terminal</i>	14.0	10.0	mm
$d_{Spb/Apb}$			<i>terminal to backside</i>	16.0	16.0	mm
V_{ISOL}	<i>isolation voltage</i>	$t = 1 \text{ second}$ $t = 1 \text{ minute}$	50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA}$		3600 3000	V V



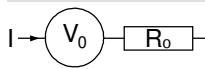
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.#(33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD200-16io1	MCD200-16io1	Box	6	498269

Equivalent Circuits for Simulation

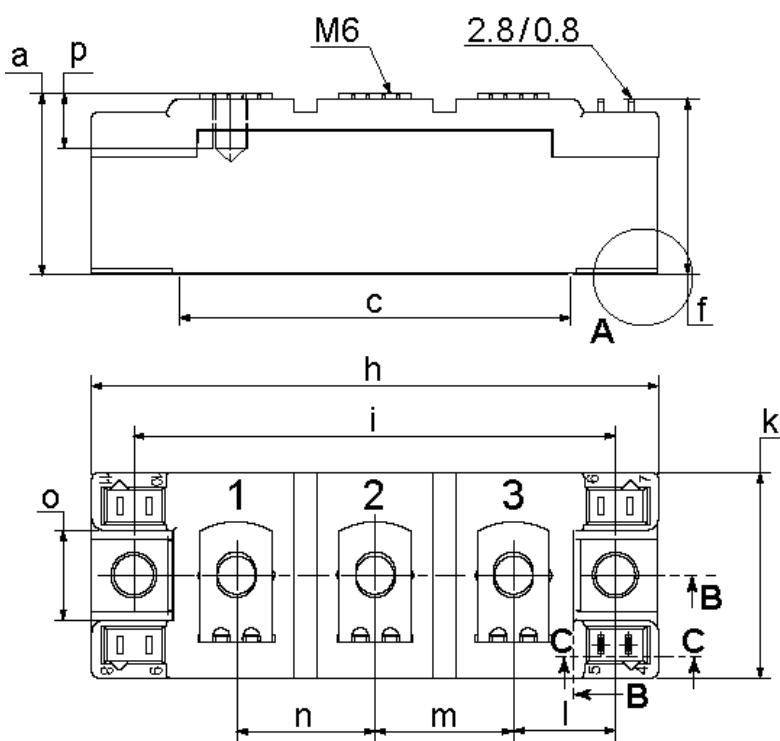
* on die level

$T_{VJ} = 125^\circ\text{C}$



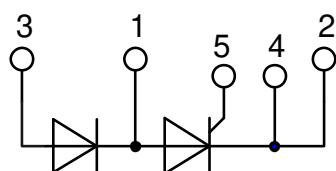
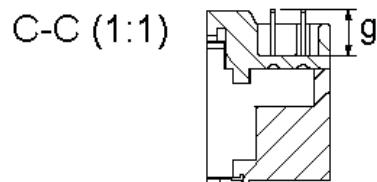
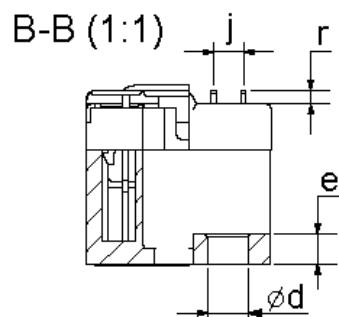
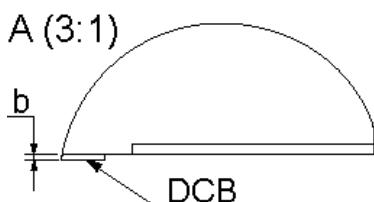
Thyristor

$V_{0\max}$ threshold voltage 0.8 V
 $R_{0\max}$ slope resistance * 0.7 mΩ

Outlines Y4


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
r	1.8	2.4	0.071	0.041

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 180L (L = Left for pin pair 4/5) UL758, style 3751


Thyristor

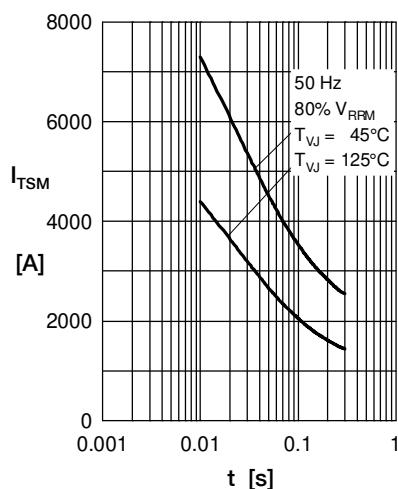


Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t : duration

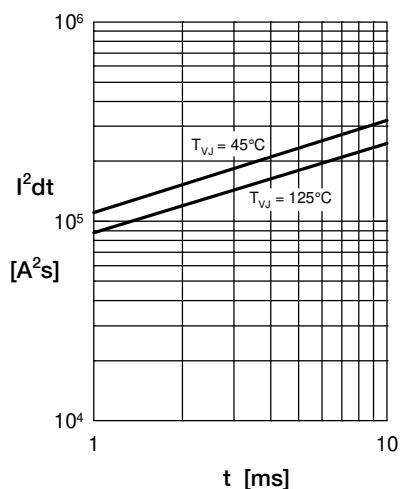


Fig. 2 I^2t versus time (1-10 ms)

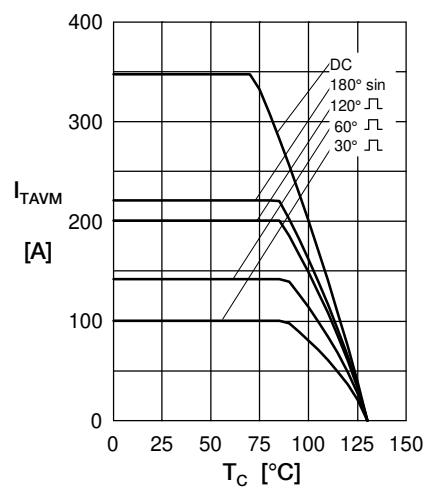


Fig. 3 Max. forward current at case temperature

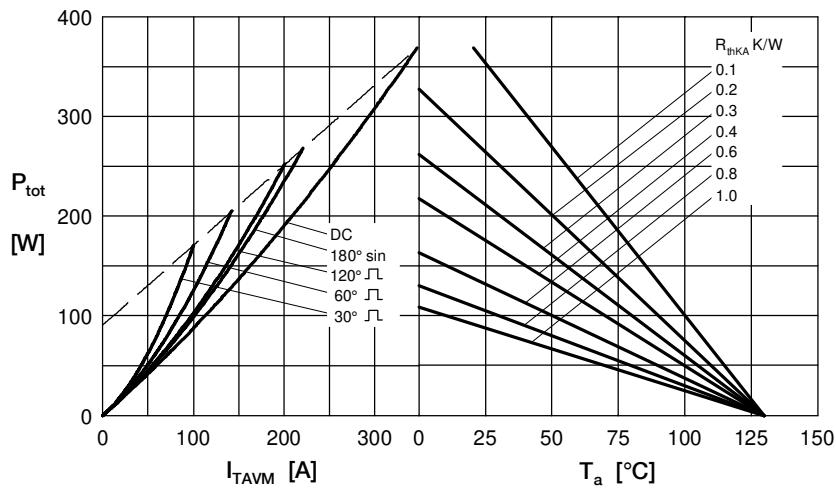


Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

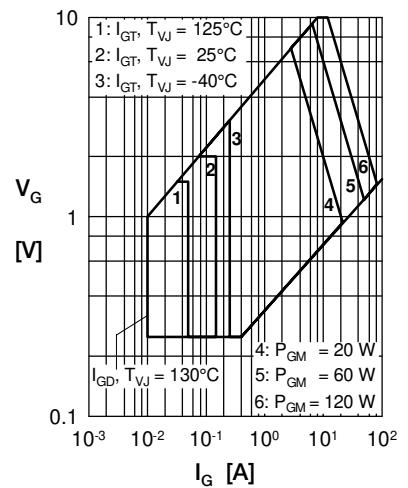


Fig. 5 Gate trigger characteristics

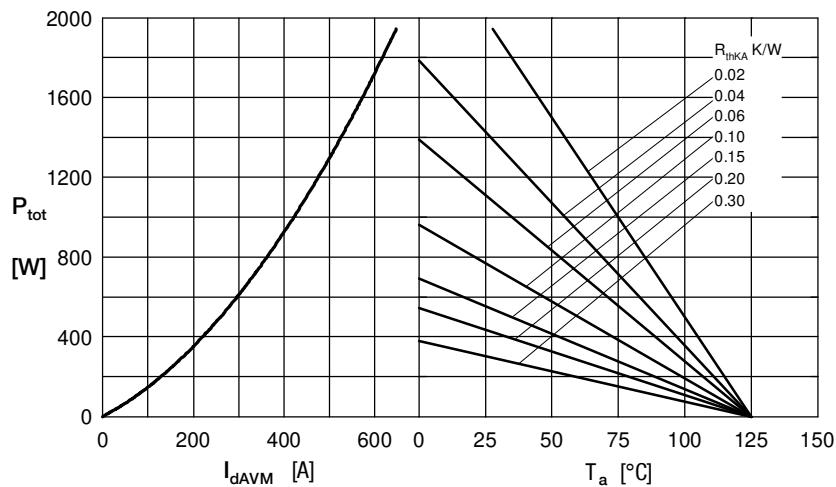


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

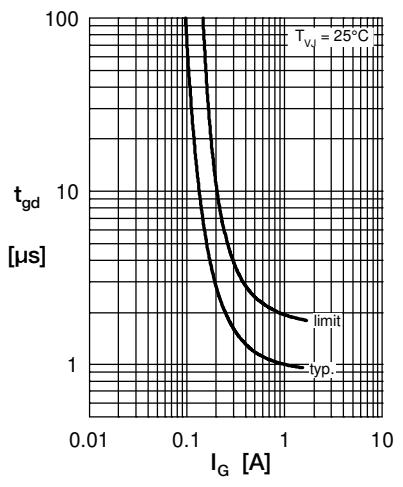


Fig. 7 Gate trigger delay time

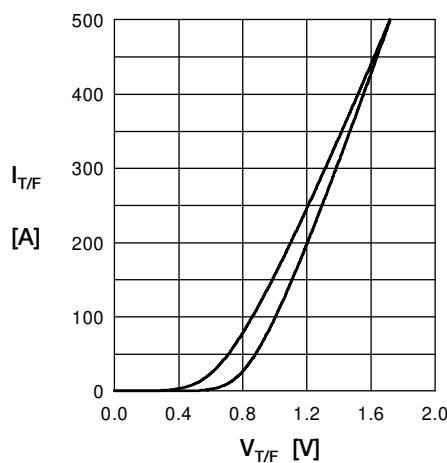
Rectifier


Fig. 8 Forward current versus voltage drop

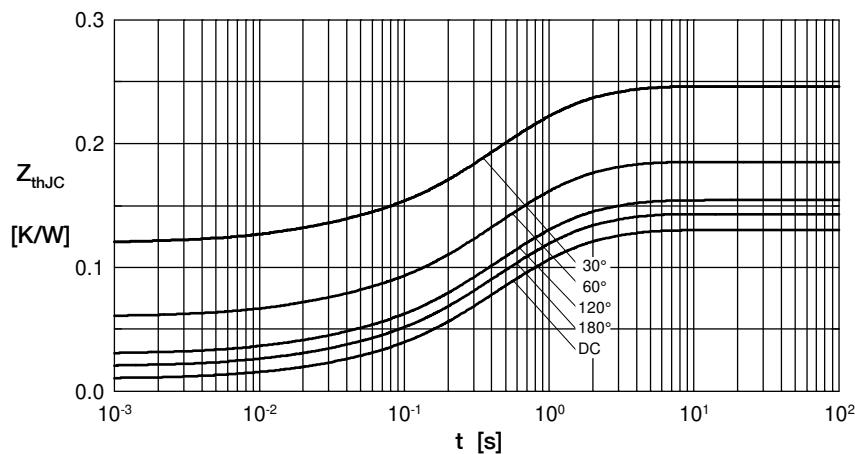


Fig. 9 Transient thermal impedance junction to case at various conduction angles

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0100	0.00014
2	0.0065	0.019
3	0.0250	0.180
4	0.0615	0.520
5	0.0270	1.600

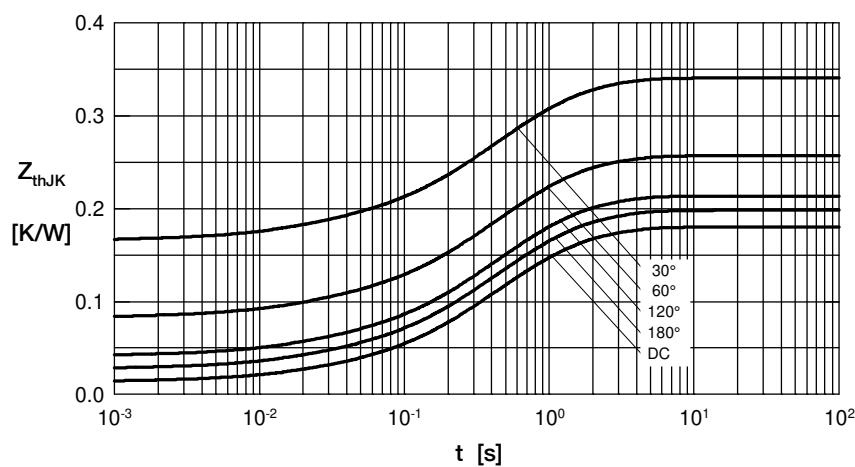


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)



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Электрон
Связь**

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